exposing said first conductive layer to an N_2/H_2 plasma to reduce an ability of the first conductive layer to associate with oxygen; and

forming the second conductive layer on the first conductive layer, the second conductive layer being formed after the first conductive layer has been exposed to the N_2/H_2 plasma.

Please add new claims 76-90 as follows:

76. (New) A method of treating a semiconductor device, comprising:

providing a capacitor having a first conductive plate, a dielectric over the first plate, and a second conductive plate over the dielectric, the second conductive plate including a tungsten nitride layer formed on the dielectric and polysilicon layer formed on the tungsten nitride layer;

exposing the tungsten nitride layer to oxygen;

exposing the tungsten nitride layer to a reducing atmosphere prior to formation of the polysilicon layer on the tungsten nitride layer; and

forming the polysilicon layer on the tungsten nitride layer, the polysilicon layer being formed after exposure of the tungsten nitride layer to oxygen and the reducing atmosphere.

77. (New) The method of claim 76 wherein the dielectric comprises tantalum pentoxide.

78. (New) The method of claim 76 wherein the reducing atmosphere comprises silane gas SiH_4.

79. (New) A method of treating a semiconductor device, comprising:

providing a capacitor having a first plate, a dielectric on the first plate, a first conductive layer on the dielectric with the first conductive layer having an ability to

associate with oxygen, an oxide layer on the first conductive layer, and a second conductive layer on the oxide layer;

exposing the capacitor to a thermal process; and

prior to exposure to the thermal process and prior to forming the second conductive layer on the first conductive layer, exposing the first conductive layer to an N_2/H_2 plasma to reduce an amount of oxygen associated with the first conductive material during formation of the second conductive layer and reduce a thickness of the oxide layer subsequently formed between the first and second conductive layers during exposure of the capacitor to the thermal process.

80. (New) The method of claim 79 wherein the thickness of the oxide layer is less than approximately 10 angstroms.

81. (New) The method of claim 79 wherein the oxide layer comprises silicon dioxide.

82. (New) The method of claim 79 wherein the dielectric comprises tantalum pentoxide.

83. (New) The method of claim 79 wherein the first conductive layer comprises tungsten nitride.

84. (New) A method of treating a semiconductor device, comprising:

providing a first conductive layer and a dielectric formed on the first conductive layer; and

prior to forming the dielectric layer, exposing the first conductive layer to an N_2/H_2 plasma to reduce the ability of the first conductive material to associate with oxygen.

85. (New) The method of claim 84 wherein the dielectric comprises tantalum pentoxide.

86. (New) The method of claim 84 wherein the first conductive layer comprises tungsten nitride.

87. (New) A method of treating a semiconductor device, comprising:

providing a first conductive plug, a first conductive layer on the plug, and a second conductive layer on the first conductive layer; and

prior to forming the second conductive layer, exposing the first conductive layer to an N_2/H_2 plasma to reduce the ability of the first conductive material to associate with oxygen.

88. (New) The method of claim 87 wherein the plug comprises at least one of polysilicon, tungsten, copper, and aluminum.

89. (New) The method of claim 87 wherein the first conductive layer comprises tungsten nitride.

90. (New) The method of claim 87 wherein the second conductive layer comprises copper.